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## Contents

- vii Conference Committee ix Organizers, Sponsors, and Cooperating Partners

## STUDENT PRESENTATIONS

	STUDENT PRESENTATIONS
13787 02	Hybrid deep learning and physics-based framework for grayscale photolithography mask generation [13787-18]
13787 03	Physics-based differentiable simulation framework for power optimization in parallel two-photon polymerization [13787-21]
	ELECTRON AND OPTICAL MULTI-BEAM MASK WRITING AND PROCESSING
13787 04	Investigation of MURA performance of the multi-beam mask writer 100 Flex, including intrawriting field and beyond [13787-43]
13787 06	Multi-beam mask writer MBM-4000 for high-NA EUV era [13787-29]
13787 07	MBMW 401 tool for 2nm and sub-2nm EUV masks [13787-46]
	EUV LITHOGRAPHY
13787 09	New insights into EUV mask modeling based on at-wavelength reflectance measurements [13787-27]
13787 0A	Comparing bright field imaging performance at 0.33 NA of a novel low-reflectivity low-n and a standard Ta-based EUV mask [13787-32]
13787 OB	Long-lifetime beryllium-based EUV pellicle membrane [13787-50]
13787 OC	Methodology of stitching evaluation at NA 0.33 to enable high-NA assessment [13787-55]
13787 OE	Advancing semiconductor patterning with EUV hyper NA: opportunities and challenges [13787-38]

	NOVEL RESIST TECHNOLOGY AND MODELING
13787 OF	A novel energy saving process for PFAS-free ArF immersion lithography [13787-13]
13787 OI	Highly parallelized RCWA with optimized eigenvalue problem for efficient simulation of curvilinear mask structures [13787-17]
	ELECTRON AND OPTICAL DIRECT WRITE
13787 OJ	Cell projection e-beam lithography for optical metastructures [13787-25]
13787 OK	Fabrication of single-electron shuttling channels in a silicon CMOS fab using high-throughput electron beam lithography [13787-39]
	MASK AND WAFER PROCESS CONTROL
13787 0M	A MetroSpection use case: enabling CNN ADC on CDSEM images for robust R&D developments and improved manufacturing quality control [13787-22]
13787 ON	Challenges and experiences with mask inspection round robin [13787-47]
	NANOIMPRINT LITHOGRAPHY (NIL) AND TWO-PHOTON LITHOGRAPHY
13787 OR	NANOIMPRINT LITHOGRAPHY (NIL) AND TWO-PHOTON LITHOGRAPHY  Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]
13787 OR	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography
13787 OR	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]
	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]  ADVANCEMENTS IN NEW APPLICATION FIELDS  Precise optical characterization of SiGe thin films for next generation transistor metrology
13787 OT	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]  ADVANCEMENTS IN NEW APPLICATION FIELDS  Precise optical characterization of SiGe thin films for next generation transistor metrology [13787-41]  Improving uptime of clustered lithography tools by smart maintenance [13787-16]
13787 OT	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]  ADVANCEMENTS IN NEW APPLICATION FIELDS  Precise optical characterization of SiGe thin films for next generation transistor metrology [13787-41]
13787 OT	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]  ADVANCEMENTS IN NEW APPLICATION FIELDS  Precise optical characterization of SiGe thin films for next generation transistor metrology [13787-41]  Improving uptime of clustered lithography tools by smart maintenance [13787-16]
13787 OT 13787 OU	Two-photon polymerization lithography as a mastering tool for nanoimprint lithography [13787-48]  ADVANCEMENTS IN NEW APPLICATION FIELDS  Precise optical characterization of SiGe thin films for next generation transistor metrology [13787-41]  Improving uptime of clustered lithography tools by smart maintenance [13787-16]  POSTER SESSION  Large-scale curvilinear photonic patterns metrology: exploring a new method based on

13787 OZ	Modeling of two-photon lithography including oxygen diffusion using a generalized compact model [13787-9]
13787 15	The performance evaluation of at-resolution stitching on NXE [13787-61]
13787 16	More nodes to be covered by multi-beam mask writers: MBM-2000C for mature nodes [13787-62]
13787 18	Modelling electric-field-assisted post-exposure bake: role of acid dissociation and dielectrophoresis [13787-44]
13787 19	Formation of dissolution-resistant top layer in EUV-CAR resist and possible impact on line edge roughness [13787-56]
13787 1A	A step and repeat and roll-to-plate nanoimprint process for the fabrication of nanostructured substrates [13787-14]
13787 1E	Evaluation of HSQ resist Medusa 84 SiH regarding suitability for various process windows [13787-57]
13787 1F	Analytical methods for SEM image enhancement: noise and charging effect reduction for precise contour extraction [13787-28]
13787 1H	Development of an intra-level mix-and-match lithography process using negative-tone photoresist AR-N 4400-10 S4 to combine i-line stepper and electron beam exposure [13787-53]
13787 1K	R2R-controlled spin speed to achieve the target layer thickness for photoresist- and ARC-materials [13787-33]
13787 1L	Overlay analysis calculator for SPC applications [13787-11]